Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("6657665").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/05 17:21
L2	21	("5012344" "5471515" "5587596" "5608243" "5625210" "5631704" "5698844" "5721425" "5760458" "5786623" "5789774" "5838650" "5847422" "5872371" "6150704" "6184516" "6466266").PN. OR ("6657665"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/10/05 17:47
L3	15	circuit with transfer with source follower with reset and @ay<="1999"	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/10/05 17:49
L4	10	circuit with transfer with source follower with reset and @ay<="1999" and "348".clas.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/10/05 18:05
L5	45	transfer with source follower with reset and @ay<="1999" and "348".clas.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/10/05 18:11
S1	147	retrograde well and cmos and @ay<="1999"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:02
S2	140	retrograde well and cmos and @ay<="1999" not durcan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:03
S3	9	retrograde well and cmos and @ay<="1999" and sensor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:25

S4	38	retrograde and cmos and @ay<="1999" and sensor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:26
S5	45	retrograde and @ay<="1999" and sensor and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:26
S6	85	retrograde and @ay<="1999" and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:31
S7	173	(doping with higher) and @ay<="1999" and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:32
S8	40	S6 not S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:31
S9	39	(doping with higher) and @ay<="1999" and (reset with transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:42
S10	919	retrograde and photo\$7 and @ay<="1999"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:42
S11	274	retrograde and photo\$8 and @ay<="1999" and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:45

S12	96	(retrograde with dop\$4) and photo\$8 and @ay<="1999" and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:47
S13	360	(257/231).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/03 18:56
S14	0	S13 and retrograde and @ay<="1999"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:56
S15	321	S13 and @ay<="1999"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:57
S16	14	S13 and @ay<="1999" and (dop\$4 with higher)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 19:00
S17	19	S13 and @ay<="1999" and (gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 18:59
S18	632	(257/233).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/03 19:00
S19	1014	(257/291).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/03 19:00

					0==	2007/10/22 12 52
S20	1187	(257/292).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/03 19:00
S21	0	("18and@ay<=1999and(dop\$4wit hhigher)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/03 19:00
S22	25	S18 and @ay<="1999" and (dop\$4 with higher)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 19:03
S23	2	(S19 or S20) and @ay<="1999" and retrograde	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 19:01
S24	1	S18 and @ay<="1999" and retrograde	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 19:01
S25	25	("5461425" "5471515" "5548773" "5665959" "5780884" "5841125" "5841126" "5850195" "5859450" "5861645" "5861655" "5869857" "5880691" "5886659" "5949483" "5965871" "5969758" "5981932" "5990506" "5995163" "6072206" "6090639").PN. OR ("6465862").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/10/03 19:02
S26	1	S25 and retrograde	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/10/03 19:01
S27	9	S25 and concentration	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/10/03 19:02

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S28	44	"6787819" "6858460" "6445014" "7166878" "6930338" US-4374700-\$.DID. OR US-5150177-\$.DID. OR US-5151385-\$.DID. OR US-5268316-\$.DID. OR US-5293237-\$.DID. OR US-5319604-\$.DID. OR US-5428239-\$.DID. OR US-5461425-\$.DID. OR US-5541402-\$.DID. OR US-55476763-\$.DID. OR US-5608243-\$.DID. OR US-5625210-\$.DID. OR US-5705846-\$.DID. OR US-5705846-\$.DID. OR US-5773863-\$.DID. OR US-5773863-\$.DID. OR US-5773863-\$.DID. OR US-5773863-\$.DID. OR US-5773863-\$.DID. OR US-5859450-\$.DID. OR US-5859450-\$.DID. OR US-6147366-\$.DID. OR US-6147366-\$.DID. OR US-6147366-\$.DID. OR US-6268250-\$.DID. OR US-6268250-\$.DID. OR	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 20:12
S29	20	(("6787819") or ("6858460") or ("6445014") or ("7166878") or ("6930338") or ("6109734") or ("5030317") or ("4775445") or ("5478606") or ("5758417")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/03 20:12
S30	18	(S28 or S29) and retrograde	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 20:12
S31	2	("5656514").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/03 20:34
S32	2	("6093951").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/03 20:37

S33	2	("5773863").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/03 20:37
S34	2	10/295952	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/10/03 21:08
S37	6	(("6787819") or ("6483129") or ("6310366")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/05 17:21

10/5/2007 6:50:19 PM
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Day: Friday Date: 10/5/2007

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Inventor Name Search Result

Your Search was:

Last Name = RHODES First Name = HOWARD

Application#	Patent#	Status	Date Filed	Title	Inventor Name
	5405788				RHODES, HOWARD
08416994	Not Issued	166	04/05/1995	METHOD FOR FORMING AND TAILORING THE ELECTRICAL CHARACTERISTICS OF SEMICONDUCTOR DEVICES	
08578825	Not Issued	161	12/26/1995	METHOD TO AVOID THRESHOLD VOLTAGE SHIFT IN THICKER DIELECTRIC FILMS	RHODES, HOWARD
08627262	5750012	150	04/04/1996	MULTIPLE SPECIES SPUTTERING FOR IMPROVED BOTTOM COVERAGE AND IMPROVED SPUTTER RATE	RHODES, HOWARD
08763848	5661045	150	12/09/1996	METHOD FOR FORMING AND TAILORING THE ELECTRICAL CHARACTERISTICS OF SEMICONDUCTOR DEVICES	RHODES, HOWARD
09053354	6083358	150	04/01/1998	MULTIPLE SPECIES SPUTTERING FOR IMPROVED BOTTOM COVERAGE AND IMPORVED SPUTTER RATE	RHODES, HOWARD
09312373	6462394	150	05/13/1999	DEVICE CONFIGURED TO AVOID THRESHOLD VOLTAGE SHIFT IN A DIELECTRIC FILM	RHODES, HOWARD
09609441	6398923	150	07/03/2000	MULTIPLE SPECIES SPUTTERING METHOD	RHODES, HOWARD
09654093	7067442	150	08/31/2000	METHOD TO AVOID THRESHOLD VOLTAGE SHIFT IN THICKER DIELECTRIC FILMS	RHODES, HOWARD

09721839	6458714	150	11/22/2000	METHOD OF SELECTIVE OXIDATION IN SEMICONDUCTOR MANUFACTURE	RHODES, HOWARD
09789335	6518610	150	02/20/2001	RHODIUM-RICH OXYGEN BARRIERS	RHODES, HOWARD
09945252	6630706	150	08/30/2001	LOCALIZED ARRAY THRESHOLD VOLTAGE IMPLANT TO ENHANCE CHARGE STORAGE WITHIN DRAM MEMORY CELLS	RHODES, HOWARD
10209386	6740554	150	07/30/2002	METHODS TO FORM RHODIUM-RICH OXYGEN BARRIERS	RHODES, HOWARD
10234576	6800520	150	08/30/2002	LOCALIZED ARRAY THRESHOLD VOLTAGE IMPLANT ENHANCE CHARGE STORAGE WITHIN DRAM MEMORY CELLS	RHODES, HOWARD
10291728	6818930	150	11/12/2002	GATED ISOLATION STRUCTURE FOR IMAGERS	RHODES, HOWARD
<u>10291772</u>	6888214	150	11/12/2002	ISOLATION TECHNIQUES FOR REDUCING DARK CURRENT IN CMOS IMAGE SENSORS	RHODES, HOWARD
<u>10293494</u>	7091536	150	11/14/2002	ISOLATION PROCESS AND STRUCTURE FOR CMOS IMAGERS	RHODES, HOWARD
10303897	6960796	150	11/26/2002	CMOS IMAGER PIXEL DESIGNS WITH STORAGE CAPACITOR	RHODES, HOWARD
10318597	<u>6781175</u>	150	12/12/2002	RHODIUM-RICH INTEGRATED CIRCUIT CAPACITOR ELECTRODE	RHODES, HOWARD
10345155	7087944	150	01/16/2003	IMAGE SENSOR HAVING A CHARGE STORAGE REGION PROVIDED WITHIN AN IMPLANT REGION	RHODES, HOWARD
10385844	6949445	150	03/12/2003	METHOD OF FORMING ANGLED IMPLANT FOR TRENCH ISOLATION	RHODES, HOWARD
10422965	Not Issued	71			RHODES, HOWARD
10437494	6815287	150		LOCALIZED ARRAY THRESHOLD VOLTAGE IMPLANT TO ENHANCE CHARGE STORAGE WITHIN	RHODES, HOWARD

				DRAM MEMORY CELLS	
10632916	6878568	150	08/04/2003	CMOS IMAGER AND METHOD OF FORMATION	RHODES, HOWARD
10655219	6969631	150	09/05/2003	METHOD OF FORMING PHOTODIODE WITH SELF- ALIGNED IMPLANTS FOR HIGH QUANTUM EFFICIENCY	RHODES, HOWARD
10660565	Not Issued	61	09/12/2003	CMOS imager pixel designs	RHODES, HOWARD
<u>10771290</u>	Not Issued	93	02/05/2004	GATED ISOLATION STUCTURE FOR IMAGERS	RHODES, HOWARD
10850664	7038263	150	05/21/2004	INTEGRATED CIRCUITS WITH RHODIUM-RICH STRUCTURES	RHODES, HOWARD
10925917	Not Issued	71	08/26/2004	Isolation techniques for reducing dark current in CMOS image sensors	RHODES, HOWARD
10926358	7239003	150	08/26/2004	ISOLATION TECHNIQUES FOR REDUCING DARK CURRENT IN CMOS IMAGE SENSORS	RHODES, HOWARD
10983971	Not Issued	160	11/08/2004	Localized array threshold voltage implant to enhance charge storage within DRAM memory cells	RHODES, HOWARD
11009006	7217589	150	12/13/2004	DEEP PHOTODIODE ISOLATION PROCESS	RHODES, HOWARD
11043998	Not Issued	93		IMAGER FLOATING DIFFUSION REGION AND PROCESS FOR FORMING SAME	RHODES, HOWARD
11066325	Not Issued	160	02/25/2005	Isolation techniques for reducing dark current in CMOS image sensors	RHODES, HOWARD
11165490	7102180	150	06/24/2005	CMOS IMAGER PIXEL DESIGNS	RHODES, HOWARD
11206125	7195947	150	08/18/2005		RHODES, HOWARD
11242375	Not Issued	30		Method to avoid threshold voltage shift in thicker dielectric films	RHODES, HOWARD
11434767	Not Issued	30		Image sensor having a charge storage region provided within an implant region	RHODES, HOWARD

11488845	Not Issued	41	07/19/2006	CMOS imager pixel designs	RHODES, HOWARD
11529631	Not Issued	30	09/29/2006	Method of operating image sensor	RHODES, HOWARD
<u>11636979</u>	Not Issued	17	12/12/2006	Photodiode with self-aligned implants for high quantum efficiency and method of formation	RHODES, HOWARD
<u>11708067</u>	Not Issued	30	02/20/2007	Photodiode with self-aligned implants for high quantum efficiency and method of formation	RHODES, HOWARD
60478348	Not Issued	159	06/16/2003	Photodiode with self-aligned implants for high quantum efficiency and method of formation	RHODES, HOWARD
60947347	Not Issued	20	06/29/2007	HIGH DYNAMIC RANGE (HDR) SENSOR WITH OVERFLOW DRAIN	RHODES, HOWARD
06130075	4307922	150	03/13/1980	MOVABLE STORAGE SYSTEM	RHODES, HOWARD A.
09207593	6639261	150	12/08/1998	METHOD FOR FORMING A LOW LEAKAGE CONTACT IN A CMOS IMAGER	RHODES, HOWARD E
09310489	6159790	150	05/12/1999	METHOD OF CONTROLLING OUTDIFFUSION IN A DOPED THREE-DIMENSIONAL FILM BY USING ANGLED IMPLANTS	RHODES, HOWARD E
09310515	<u>6211545</u>	150	05/12/1999	A DEVICE FABRICATED BY A METHOD OF CONTROLLING OUTDIFFUSION FROM A DOPED THREE-DIMENSIONAL FILM	HOWARD E.
09513470	6407440	150	02/25/2000	PIXEL CELL WITH HIGH STORAGE CAPACITANCE FOR A CMOS IMAGER	RHODES, HOWARD E.
09516819	6285038	150		Integrated circuitry and dram integrated circuitry	RHODES, HOWARD E.

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Last Name = DURCAN First Name = MARK

Application#	Patent#	Status	Date Filed	Title	Inventor Name
07526079	Not Issued	==		METHOD FOR REDUCING CROSS-SECTIONAL ASYMMETRY IN SPACER STRIPS USED AS MASK ELEMENTS IN A PROCESS FOR REDUCING MINIMUM PHOTOLITHOGRAPHIC MASKING PITCH	DURCAN, MARK
08862752	6331488	150	05/23/1997	PLANARIZATION PROCESS FOR SEMICONDUCTOR SUBSTRATES	DURCAN, MARK
<u>09146116</u>	6333264	150	09/02/1998	SEMICONDUCTOR PROCESSING METHOD USING HIGH PRESSURE LIQUID MEDIA TREATMENT	DURCAN, MARK
09311914	6100162	150	05/14/1999	METHOD OF FORMING A CIRCUITRY ISOLATION REGION WITHIN A SEMICONDUCTIVE WAFER	DURCAN, MARK
09334261	6310366	150	06/16/1999	RETROGRADE WELL STRUCTURE FOR A CMOS IMAGER	DURCAN, MARK
09518558	6340624	150	03/03/2000	Method of forming a circuitry isolation region within a semiconductive wafer	DURCAN, MARK
09603849	6417102	150	06/26/2000	SEMICONDUCTOR PROCESSING METHOD USING HIGH PRESSURE LIQUID MEDIA TREATMENT	DURCAN, MARK
09645582	6445014	150	08/25/2000	RETROGRADE WELL STRUCTURE FOR A CMOS IMAGER	DURCAN, MARK
09832560	6743724	150		PLANARIZATION PROCESS FOR SEMICONDUCTOR	DURCAN, MARK

				SUBSTRATES	
09918450	6483129	150	08/01/2001	RETROGRADE WELL STRUCTURE FOR A CMOS IMAGER	DURCAN, MARK
10180088	6686220	150	06/27/2002	RETROGRADE WELL STRUCTURE FOR A CMOS IMAGER	DURCAN, MARK
<u>10291670</u>	6858460	150	11/12/2002	RETROGRADE WELL STRUCTURE FOR A CMOS IMAGER	DURCAN, MARK
10295952	6787819	150	11/18/2002	RETROGRADE WELL STRUCTURE FOR A CMOS IMAGER	DURCAN, MARK
10705707	6806137	150	11/11/2003	TRENCH BURIED BIT LINE MEMORY DEVICES AND METHODS THEREOF	DURCAN, MARK
10761319	Not Issued	30	01/22/2004	Retrograde well structure for a CMOS imager	DURCAN, MARK
10838545	Not Issued	41	05/04/2004	Planarization process for semiconductor substrates	DURCAN, MARK
10968429	7170124	150	10/19/2004	TRENCH BURIED BIT LINE MEMORY DEVICES AND METHODS THEREOF	DURCAN, MARK
11484809	Not Issued	168	07/11/2006	Planarization process for semiconductor substrates	DURCAN, MARK
11588748	Not Issued	41	10/27/2006	Trench buried bit line memory devices and methods thereof	DURCAN, MARK
09503638	6777732	150	02/14/2000	RANDOM ACCESS MEMORY	DURCAN, MARK D.

Inventor Search Completed: No Records to Display.

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